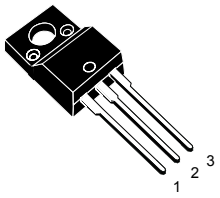
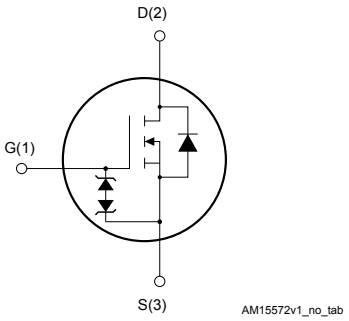
N-channel 600 V, 165 mΩ typ., 18 A, MDmesh™ DM6 Power MOSFET in a TO-220FP package



TO-220FP



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STF26N60DM6	600 V	195 mΩ	18 A

- Fast-recovery body diode
- Lower $R_{DS(on)}$ per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh™ DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge (Q_{rr}), recovery time (t_{rr}) and excellent improvement in $R_{DS(on)}$ per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.

Product status link
STF26N60DM6

Product summary	
Order code	STF26N60DM6
Marking	26N60DM6
Package	TO-220FP
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	18	A
	Drain current (continuous) at T_C = 100 °C	11	A
I_{DM}(1)	Drain current (pulsed)	60	A
P_{TOT}	Total power dissipation at T_C = 25 °C	30	W
dv/dt(2)	Peak diode recovery voltage slope	50	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	100	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T_C = 25 °C)	2.5	kV
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		

1. *Pulse width is limited by safe operating area.*
2. *I_{SD} ≤ 18 A, di/dt ≤ 900 A/µs, $V_{DS(peak)}$ < $V_{(BR)DSS}$, V_{DD} = 400 V*
3. *V_{DS} ≤ 480 V*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	4.17	°C/W
$R_{thj\text{-}amb}$(1)	Thermal resistance junction-ambient	50	°C/W

1. *When mounted on FR-4 board of inch², 2oz Cu.*

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	4	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	360	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			5	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C(1)			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 9 A		165	195	mΩ

1. *Defined by design, not subject to production test.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	940	-	pF
C_{oss}	Output capacitance		-	75	-	pF
C_{rss}	Reverse transfer capacitance		-	4	-	pF
$C_{oss\ eq.}$(1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	157	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	4.8	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 18 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	24	-	nC
Q_{gs}	Gate-source charge		-	6	-	nC
Q_{gd}	Gate-drain charge		-	11.5	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 9 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	13	-	ns
t_r	Rise time		-	11	-	ns
$t_{d(off)}$	Turn-off delay time		-	39	-	ns
t_f	Fall time		-	8	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		18	A
I_{SDM}(1)	Source-drain current (pulsed)		-		60	A
V_{SD}(2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 18 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 18 A, di/dt = 100 A/µs, V_{DD} = 60 V (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	100		ns
Q_{rr}	Reverse recovery charge		-	0.35		µC
I_{RRM}	Reverse recovery current		-	7		A
t_{rr}	Reverse recovery time	I_{SD} = 18 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	170		ns
Q_{rr}	Reverse recovery charge		-	1.02		µC
I_{RRM}	Reverse recovery current		-	12		A

1. *Pulse width is limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5 %.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

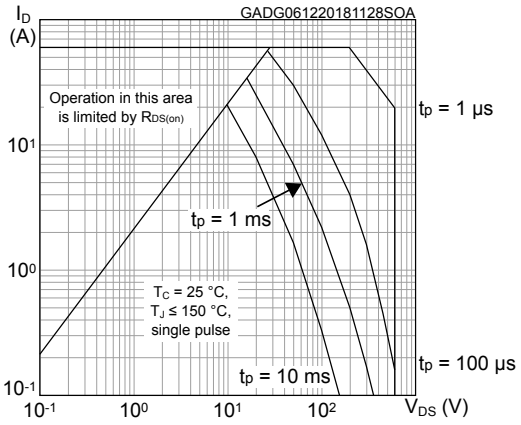


Figure 2. Normalized thermal impedance

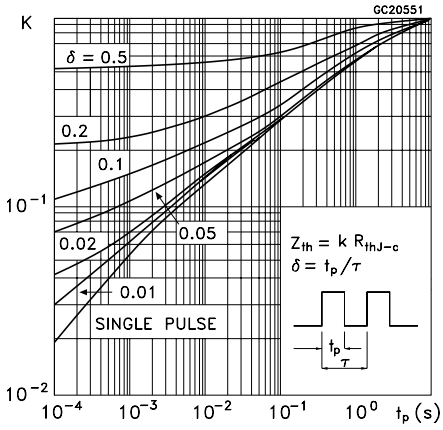


Figure 3. Output characteristics

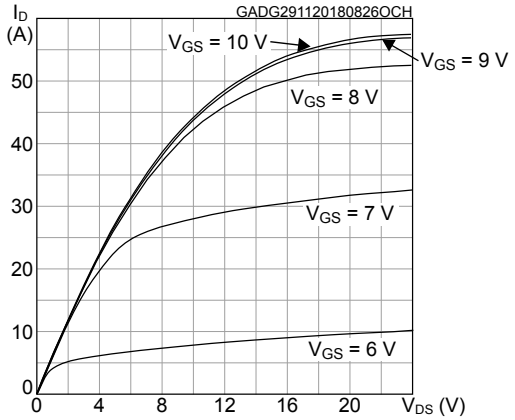


Figure 4. Transfer characteristics

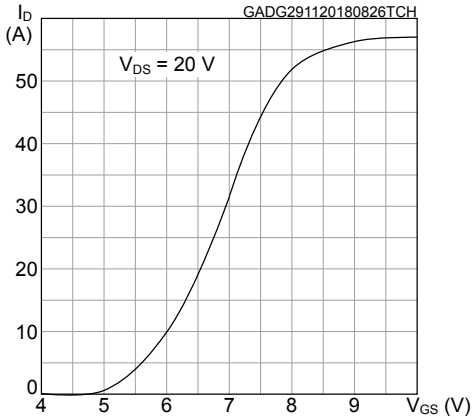


Figure 5. Gate charge vs gate-source voltage

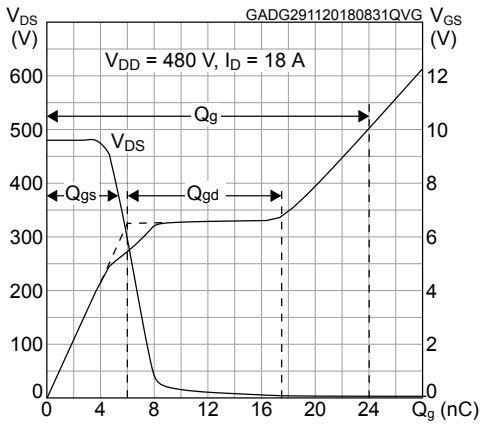


Figure 6. Capacitance variations

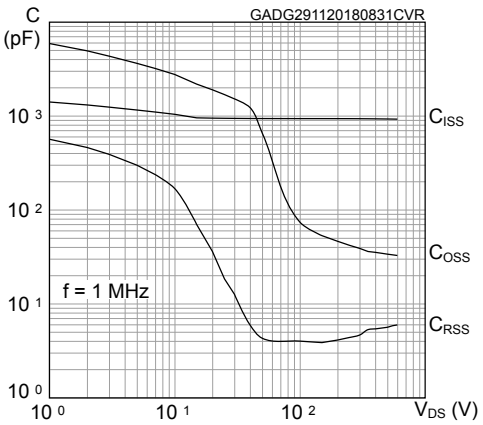


Figure 7. Static drain-source on-resistance

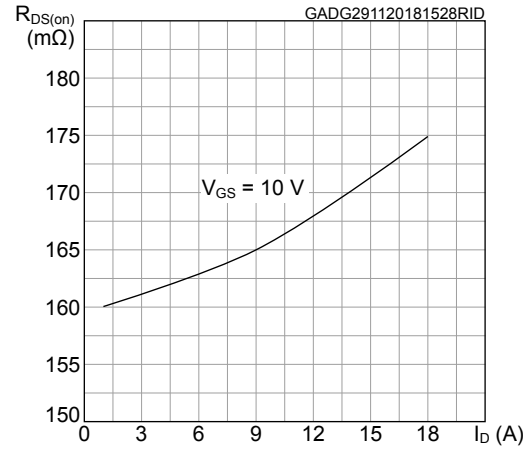


Figure 8. Normalized on-resistance vs temperature

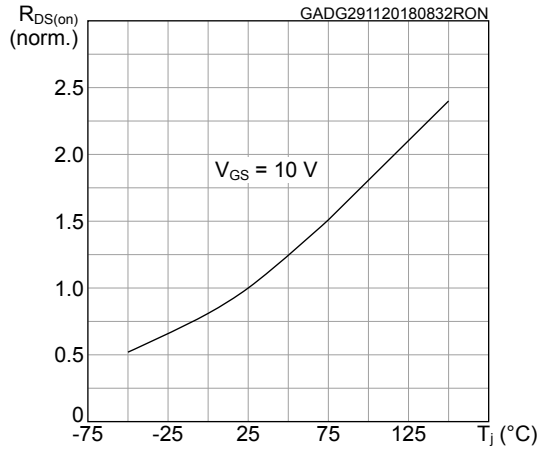


Figure 9. Normalized gate threshold voltage vs temperature

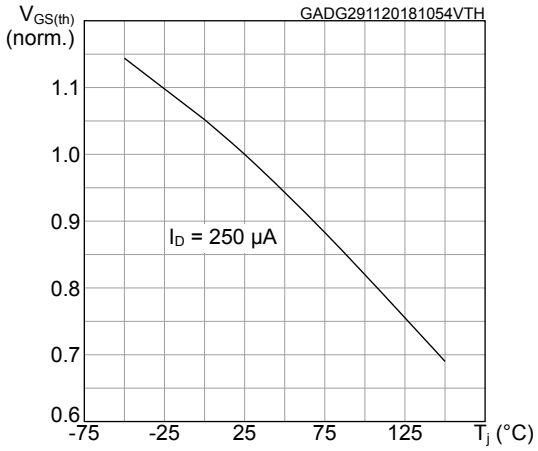


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

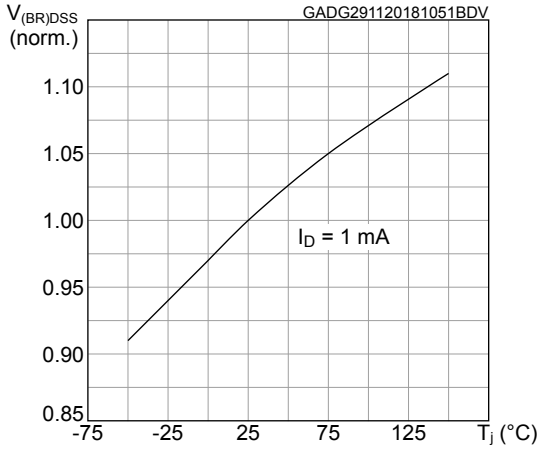


Figure 11. Output capacitance stored energy

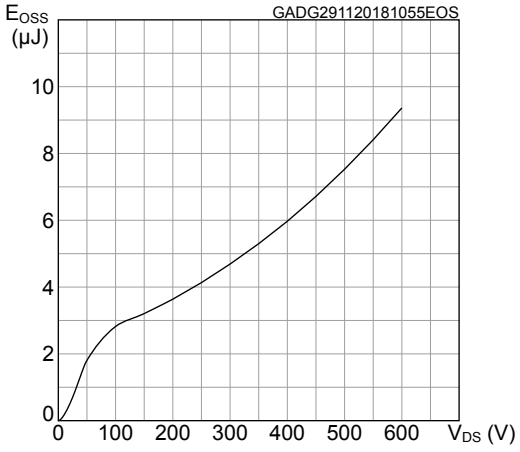
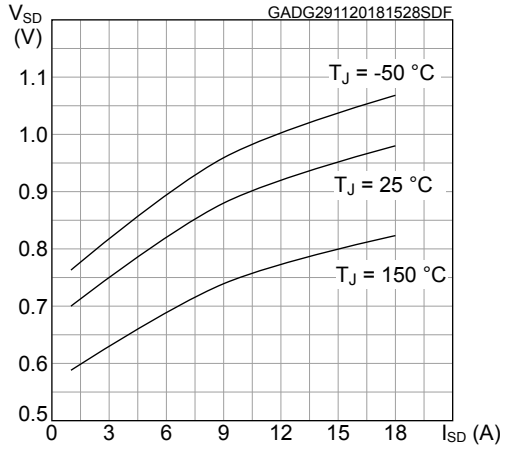


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Test circuit for resistive load switching times

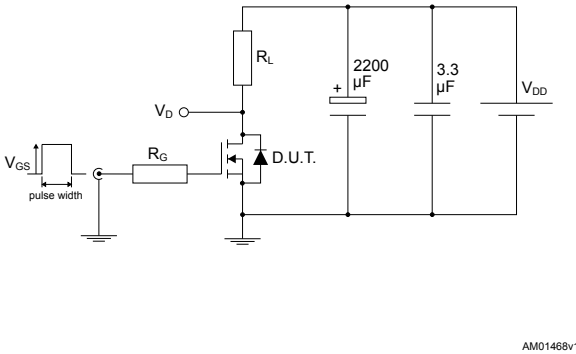


Figure 14. Test circuit for gate charge behavior

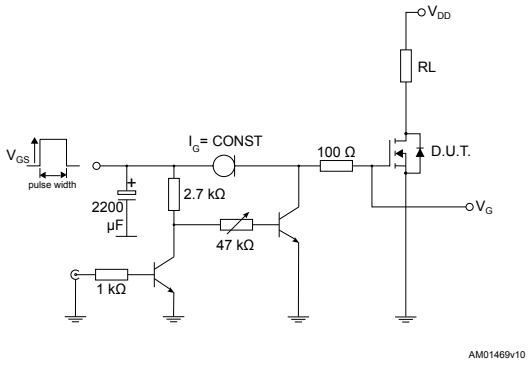


Figure 15. Test circuit for inductive load switching and diode recovery times

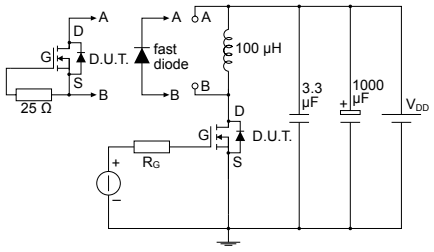


Figure 16. Unclamped inductive load test circuit

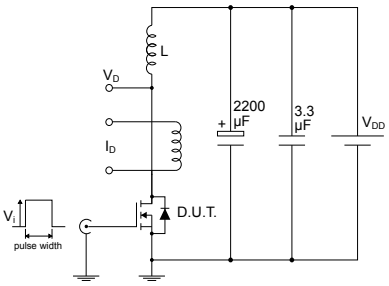


Figure 17. Unclamped inductive waveform

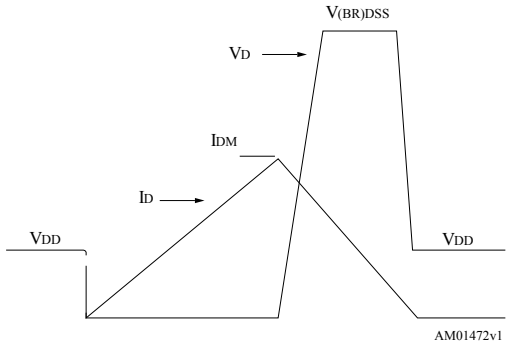
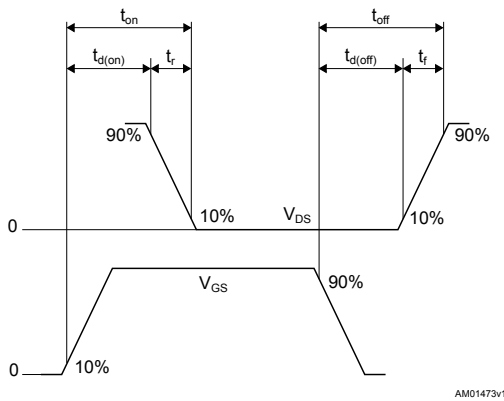


Figure 18. Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-220FP package information

Figure 19. **TO-220FP package outline**

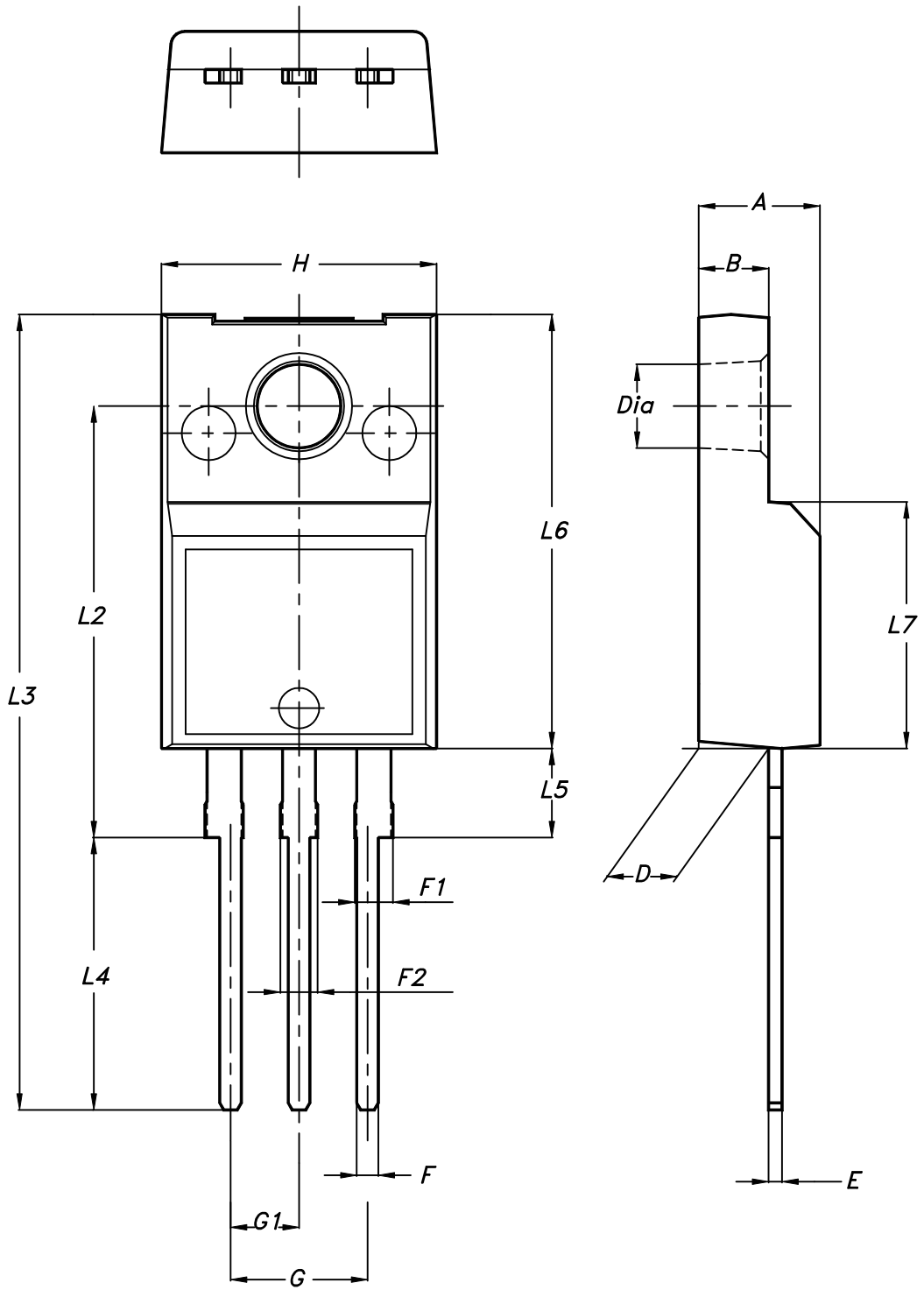


Table 8. **TO-220FP package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Revision history

Table 9. **Document revision history**

Date	Version	Changes
07-Dec-2018	1	First release.

Contents

1 **Electrical ratings** 2
2 **Electrical characteristics** 3
2.1 Electrical characteristics (curves) 5
3 **Test circuits** 7
4 **Package information** 8
4.1 TO-220FP package information 8
Revision history 11

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2018 STMicroelectronics – All rights reserved